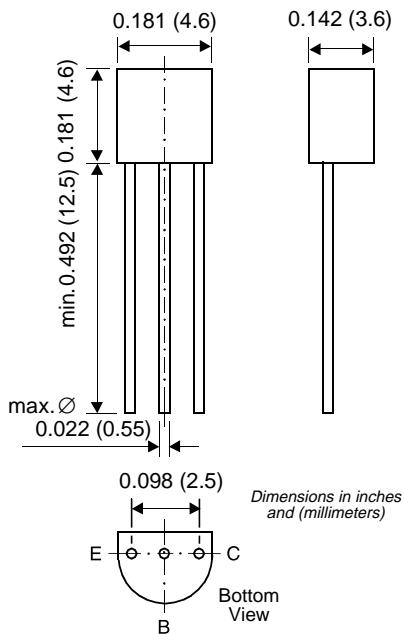




TO-226AA (TO-92)



Small Signal Transistor (PNP)

Features

- PNP Silicon Epitaxial Planar Transistor for switching and amplifier applications.
- As complementary type, the NPN transistor 2N3904 is recommended.
- On special request, this transistor is also manufactured in the pin configuration TO-18.
- This transistor is also available in the SOT-23 case with the type designation MMBT3906.

Mechanical Data

Case: TO-92 Plastic Package

Weight: approx. 0.18g

Packaging Codes/Options:

E6/Bulk - 5K per container

E7/4K per Ammo tape

Maximum Ratings & Thermal Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Parameters	Symbols	Value	Units
Collector-Emitter Voltage	-V _{C EO}	40	V
Collector-Base Voltage	-V _{CBO}	40	V
Emitter-Base Voltage	-V _{EBO}	5.0	V
Collector Current	-I _C	200	mA
Power Dissipation	T _A = 25°C T _C = 25°C	P _{tot}	mW W
Thermal Resistance Junction to Ambient Air	R _{θJA}	250 ⁽¹⁾	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _s	- 65 to +150	°C

Notes: (1) Valid provided that leads are kept at ambient temperature.

Small Signal Transistor (PNP)

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
DC Current Gain	h_{FE}	-V _{CE} = 1 V, -I _C = 0.1 mA	60	—	—	—
		-V _{CE} = 1 V, -I _C = 1 mA	80	—	—	—
		-V _{CE} = 1 V, -I _C = 10 mA	100	—	300	—
		-V _{CE} = 1 V, -I _C = 50 mA	60	—	—	—
		-V _{CE} = 1 V, -I _C = 100 mA	30	—	—	—
Collector-Emitter Cutoff Current	-I _{CEV}	-V _{EB} = 3 V, -V _{CE} = 30 V	—	—	50	nA
Emitter-Base Cutoff Current	-I _{EBV}	-V _{EB} = 3 V, -V _{CE} = 30 V	—	—	50	nA
Collector Saturation Voltage	-V _{CEsat}	-I _C = 10 mA, -I _B = 1 mA	—	—	0.25	V
		-I _C = 50 mA, -I _B = 5 mA	—	—	0.4	V
Base Saturation Voltage	-V _{BEsat}	-I _C = 10 mA, -I _B = 1 mA	—	—	0.85	V
		-I _C = 50 mA, -I _B = 5 mA	—	—	0.95	V
Collector-Emitter Breakdown Voltage	-V _{(BR)CEO}	-I _C = 1 mA, I _B = 0	40	—	—	V
Collector-Base Breakdown Voltage	-V _{(BR)CBO}	-I _C = 10 μ A, I _E = 0	40	—	—	V
Emitter-Base Breakdown Voltage	-V _{(BR)EBO}	-I _E = 10 μ A, I _C = 0	5	—	—	V
Input Impedance	h_{ie}	-V _{CE} = 10 V, -I _C = 1 mA, $f = 1 \text{ kHz}$	1	—	10	k Ω
Voltage Feedback Ratio	h_{re}	-V _{CE} = 10 V, -I _C = 1 mA, $f = 1 \text{ kHz}$	$0.5 \cdot 10^{-4}$	—	$8 \cdot 10^{-4}$	—
Current Gain-Bandwidth Product	f_T	-V _{CE} = 20 V, -I _C = 10 mA $f = 100 \text{ MHz}$	250	—	—	MHz
Collector-Base Capacitance	C _{CB} O	-V _{CB} = 5 V, $f = 100 \text{ kHz}$	—	—	4.5	pF
Emitter-Base Capacitance	C _{EB} O	-V _{EB} = 0.5 V, $f = 100 \text{ kHz}$	—	—	10	pF
Small Signal Current Gain	h_{fe}	-V _{CE} = 10 V, -I _C = 1 mA $f = 1 \text{ kHz}$	100	—	400	—
Output Admittance	h_{oe}	-V _{CE} = 1 V, -I _C = 1 mA $f = 1 \text{ kHz}$	1	—	40	μS

Small Signal Transistor (PNP)

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Noise Figure	NF	$-V_{CE} = 5 \text{ V}$, $-I_C = 100 \mu\text{A}$, $R_G = 1 \text{ k}\Omega$, $f = 10\text{...}15000 \text{ Hz}$	—	—	4	dB
Delay Time (see fig. 1)	t_d	$-I_{B1} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	—	—	35	ns
Rise Time (see fig. 1)	t_r	$-I_{B1} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$,	—	—	35	ns
Storage Time (see fig. 2)	t_s	$I_{B1} = -I_{B2} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	—	—	225	ns
Fall Time (see fig. 2)	t_f	$I_{B1} = -I_{B2} = 1 \text{ mA}$, $-I_C = 10 \text{ mA}$	—	—	75	ns

Fig. 1: Test circuit for delay and rise time

* total shunt capacitance of test jig and connectors

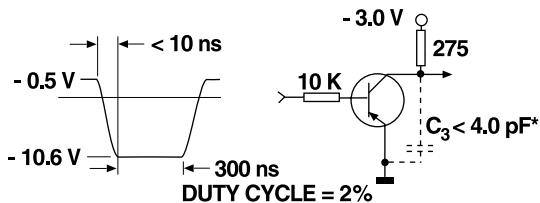


Fig. 2: Test circuit for storage and fall time

* total shunt capacitance of test jig and connectors

